

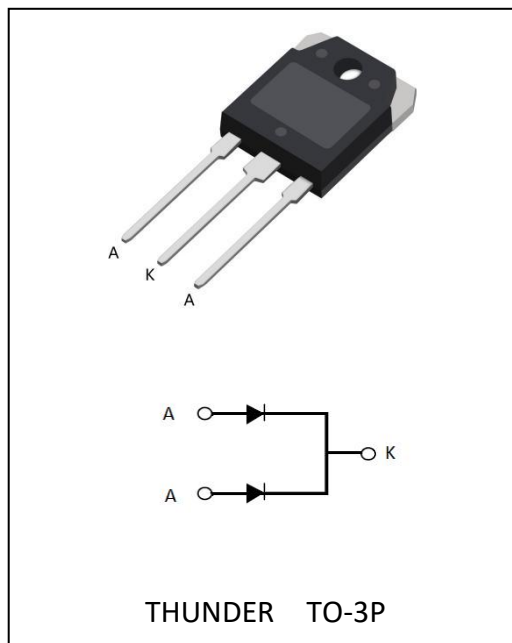
FRED

Ultrafast Soft Recovery Diode, 30A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction

Product Summary	
V_R	1200 V
$I_{F(AV)}$	2*15A
t_{rr}	32 ns



Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings

Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current	$I_{F(AV)}$	$T_c = 110^\circ\text{C}$	30	A
Single pulse forward current	I_{FSM}	$T_c = 25^\circ\text{C}$	300	
Maximum repetitive forward current	I_{FRM}	Square wave, 20kHz	36	
Operating junction	T_j		175	$^\circ\text{C}$
Storage temperatures	T_{stg}		-55 to +175	$^\circ\text{C}$

Electrical characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Breakdown voltage Blocking voltage	V_{BR} , V_R	$I_R=100\mu A$	1200			V
Forward voltage (Per Diode)	V_F	$I_F=15A$		1.8	2.50	
		$I_F=15A, T_J=125^\circ C$		1.50	2.4	
Reverse leakage current(Per Diode)	I_R	$V_R=V_{RRM}$			20	μA
		$T_J=150^\circ C, V_R=1200V$			200	
Reverse recovery time(Per Diode)	t_{rr}	$I_F=0.5A, I_R=1A, I_{RR}=0.25A$		50	60	ns
		$I_F=1A, V_R=30V, di/dt=200A/\mu s$		32	50	

Thermal characteristics

Paramter	Symbol	Typ.	Units
Junction-to-Case	$R_{\theta JC}$	0.8	$^\circ C/W$

Electrical performance (typical)

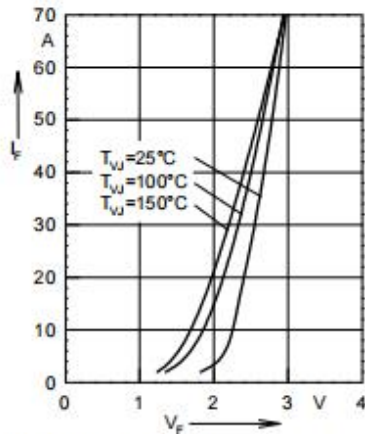


Fig. 1 Forward current versus voltage drop.

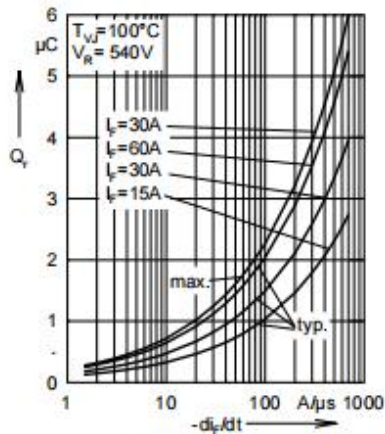


Fig. 2 Recovery charge versus $-di_F/dt$.

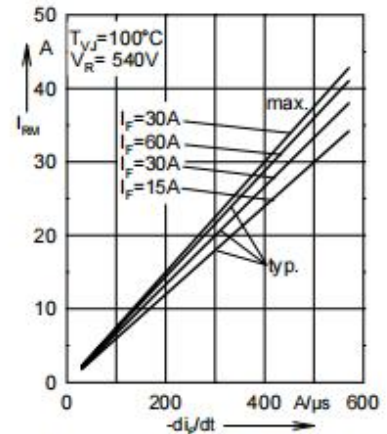


Fig. 3 Peak reverse current versus $-di_F/dt$.

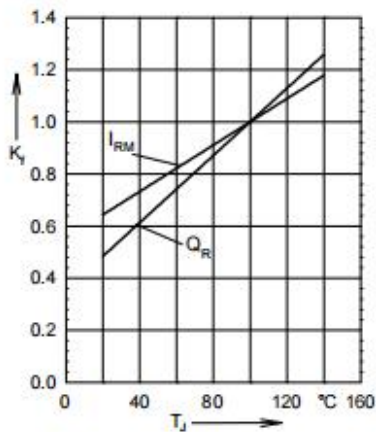


Fig. 4 Dynamic parameters versus junction temperature.

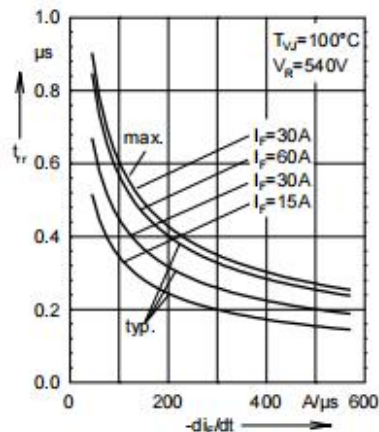


Fig. 5 Recovery time versus $-di_F/dt$.

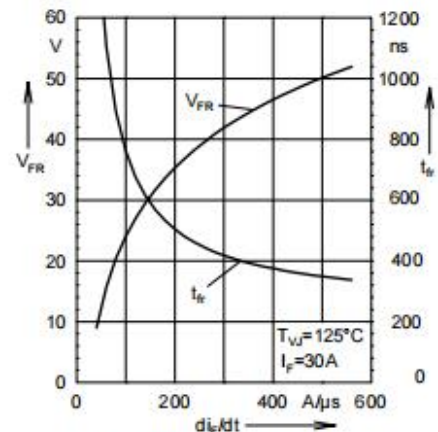


Fig. 6 Peak forward voltage versus di_F/dt .

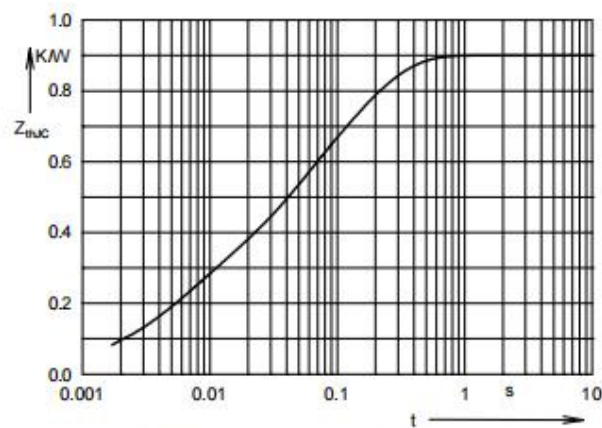
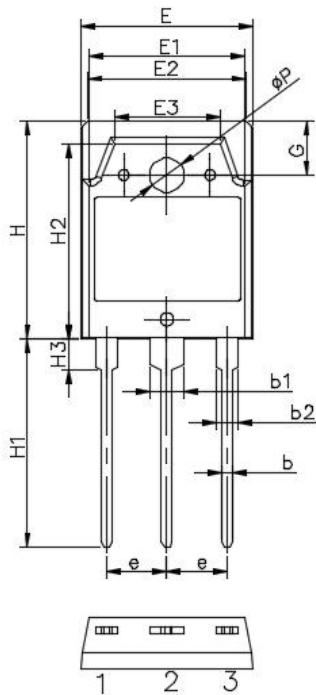


Fig. 7 Transient thermal impedance junction to case.

Package Information

TO-3P PACKAGE

基本尺寸



Symbol	单位 mm		
	Min	Nom	Max
A	4.60	4.80	5.00
A1	1.3	1.5	1.7
A2	1.20	1.40	1.60
b	0.80	1.0	1.20
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.2	15.6	16.0
E1	13.2	13.4	13.6
E2	13.1	13.3	13.5
E3	9.1	9.3	9.5
H	19.8	20.0	20.2
H1	20.1	20.3	20.5
H2	18.5	18.7	18.9
H3	3.2	3.5	3.8
G	4.8	5.0	5.2
ΦP	3.00	3.20	3.40

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